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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	216
Number of Logic Elements/Cells	1728
Total RAM Bits	12288
Number of I/O	147
Number of Gates	69000
Voltage - Supply	4.75V ~ 5.25V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	208-BFQFP Exposed Pad
Supplier Device Package	208-RQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k30rc208-3n

For more information, see the following documents:

- *Configuration Devices for APEX & FLEX Devices Data Sheet*
- *BitBlaster Serial Download Cable Data Sheet*
- *ByteBlasterMV Parallel Port Download Cable Data Sheet*
- *Application Note 116 (Configuring APEX 20K, FLEX 10K & FLEX 6000 Devices)*

FLEX 10K devices are supported by Altera development systems; single, integrated packages that offer schematic, text (including AHDL), and waveform design entry, compilation and logic synthesis, full simulation and worst-case timing analysis, and device configuration. The Altera software provides EDIF 2 0 0 and 3 0 0, LPM, VHDL, Verilog HDL, and other interfaces for additional design entry and simulation support from other industry-standard PC- and UNIX workstation-based EDA tools.

The Altera software works easily with common gate array EDA tools for synthesis and simulation. For example, the Altera software can generate Verilog HDL files for simulation with tools such as Cadence Verilog-XL. Additionally, the Altera software contains EDA libraries that use device-specific features such as carry chains which are used for fast counter and arithmetic functions. For instance, the Synopsys Design Compiler library supplied with the Altera development systems include DesignWare functions that are optimized for the FLEX 10K architecture.

The Altera development systems run on Windows-based PCs and Sun SPARCstation, and HP 9000 Series 700/800 workstations.

See the *MAX+PLUS II Programmable Logic Development System & Software Data Sheet* for more information.

Functional Description

Each FLEX 10K device contains an embedded array to implement memory and specialized logic functions, and a logic array to implement general logic.

The embedded array consists of a series of EABs. When implementing memory functions, each EAB provides 2,048 bits, which can be used to create RAM, ROM, dual-port RAM, or first-in first-out (FIFO) functions. When implementing logic, each EAB can contribute 100 to 600 gates towards complex logic functions, such as multipliers, microcontrollers, state machines, and DSP functions. EABs can be used independently, or multiple EABs can be combined to implement larger functions.

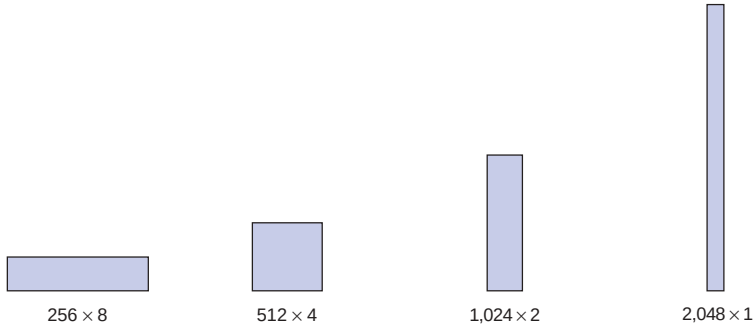
Logic functions are implemented by programming the EAB with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement a 4 × 4 multiplier with eight inputs and eight outputs. Parameterized functions such as LPM functions can automatically take advantage of the EAB.

The EAB provides advantages over FPGAs, which implement on-board RAM as arrays of small, distributed RAM blocks. These FPGA RAM blocks contain delays that are less predictable as the size of the RAM increases. In addition, FPGA RAM blocks are prone to routing problems because small blocks of RAM must be connected together to make larger blocks. In contrast, EABs can be used to implement large, dedicated blocks of RAM that eliminate these timing and routing concerns.

EABs can be used to implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the EAB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. A circuit using the EAB's self-timed RAM need only meet the setup and hold time specifications of the global clock.

When used as RAM, each EAB can be configured in any of the following sizes: 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. See Figure 2.

Figure 2. EAB Memory Configurations



During compilation, the Compiler automatically selects the best control signal implementation. Because the clear and preset functions are active-low, the Compiler automatically assigns a logic high to an unused clear or preset.

The clear and preset logic is implemented in one of the following six modes chosen during design entry:

- Asynchronous clear
- Asynchronous preset
- Asynchronous clear and preset
- Asynchronous load with clear
- Asynchronous load with preset
- Asynchronous load without clear or preset

In addition to the six clear and preset modes, FLEX 10K devices provide a chip-wide reset pin that can reset all registers in the device. Use of this feature is set during design entry. In any of the clear and preset modes, the chip-wide reset overrides all other signals. Registers with asynchronous presets may be preset when the chip-wide reset is asserted. Inversion can be used to implement the asynchronous preset. Figure 10 shows examples of how to enter a section of a design for the desired functionality.

FastTrack Interconnect

In the FLEX 10K architecture, connections between LEs and device I/O pins are provided by the FastTrack Interconnect, which is a series of continuous horizontal and vertical routing channels that traverse the device. This global routing structure provides predictable performance, even in complex designs. In contrast, the segmented routing in FPGAs requires switch matrices to connect a variable number of routing paths, increasing the delays between logic resources and reducing performance.

The FastTrack Interconnect consists of row and column interconnect channels that span the entire device. Each row of LABs is served by a dedicated row interconnect. The row interconnect can drive I/O pins and feed other LABs in the device. The column interconnect routes signals between rows and can drive I/O pins.

A row channel can be driven by an LE or by one of three column channels. These four signals feed dual 4-to-1 multiplexers that connect to two specific row channels. These multiplexers, which are connected to each LE, allow column channels to drive row channels even when all eight LEs in an LAB drive the row interconnect.

Each column of LABs is served by a dedicated column interconnect. The column interconnect can then drive I/O pins or another row's interconnect to route the signals to other LABs in the device. A signal from the column interconnect, which can be either the output of an LE or an input from an I/O pin, must be routed to the row interconnect before it can enter an LAB or EAB. Each row channel that is driven by an IOE or EAB can drive one specific column channel.

Access to row and column channels can be switched between LEs in adjacent pairs of LABs. For example, an LE in one LAB can drive the row and column channels normally driven by a particular LE in the adjacent LAB in the same row, and vice versa. This routing flexibility enables routing resources to be used more efficiently. See Figure 11.

Table 8. EPF10K10, EPF10K20, EPF10K30, EPF10K40 & EPF10K50 Peripheral Bus Sources

Peripheral Control Signal	EPF10K10 EPF10K10A	EPF10K20	EPF10K30 EPF10K30A	EPF10K40	EPF10K50 EPF10K50V
OE0	Row A	Row A	Row A	Row A	Row A
OE1	Row A	Row B	Row B	Row C	Row B
OE2	Row B	Row C	Row C	Row D	Row D
OE3	Row B	Row D	Row D	Row E	Row F
OE4	Row C	Row E	Row E	Row F	Row H
OE5	Row C	Row F	Row F	Row G	Row J
CLKENA0/CLK0/GLOBAL0	Row A	Row A	Row A	Row B	Row A
CLKENA1/OE6/GLOBAL1	Row A	Row B	Row B	Row C	Row C
CLKENA2/CLR0	Row B	Row C	Row C	Row D	Row E
CLKENA3/OE7/GLOBAL2	Row B	Row D	Row D	Row E	Row G
CLKENA4/CLR1	Row C	Row E	Row E	Row F	Row I
CLKENA5/CLK1/GLOBAL3	Row C	Row F	Row F	Row H	Row J

Table 9. EPF10K70, EPF10K100, EPF10K130V & EPF10K250A Peripheral Bus Sources

Peripheral Control Signal	EPF10K70	EPF10K100 EPF10K100A	EPF10K130V	EPF10K250A
OE0	Row A	Row A	Row C	Row E
OE1	Row B	Row C	Row E	Row G
OE2	Row D	Row E	Row G	Row I
OE3	Row I	Row L	Row N	Row P
OE4	Row G	Row I	Row K	Row M
OE5	Row H	Row K	Row M	Row O
CLKENA0/CLK0/GLOBAL0	Row E	Row F	Row H	Row J
CLKENA1/OE6/GLOBAL1	Row C	Row D	Row F	Row H
CLKENA2/CLR0	Row B	Row B	Row D	Row F
CLKENA3/OE7/GLOBAL2	Row F	Row H	Row J	Row L
CLKENA4/CLR1	Row H	Row J	Row L	Row N
CLKENA5/CLK1/GLOBAL3	Row E	Row G	Row I	Row K

Slew-Rate Control

The output buffer in each IOE has an adjustable output slew rate that can be configured for low-noise or high-speed performance. A slower slew rate reduces system noise and adds a maximum delay of approximately 2.9 ns. The fast slew rate should be used for speed-critical outputs in systems that are adequately protected against noise. Designers can specify the slew rate on a pin-by-pin basis during design entry or assign a default slew rate to all pins on a device-wide basis. The slow slew rate setting affects only the falling edge of the output.

Open-Drain Output Option

FLEX 10K devices provide an optional open-drain (electrically equivalent to an open-collector) output for each I/O pin. This open-drain output enables the device to provide system-level control signals (e.g., interrupt and write enable signals) that can be asserted by any of several devices. It can also provide an additional wired-OR plane. Additionally, the Altera software can convert tri-state buffers with grounded data inputs to open-drain pins automatically.

Open-drain output pins on FLEX 10K devices (with a pull-up resistor to the 5.0-V supply) can drive 5.0-V CMOS input pins that require a V_{IH} of 3.5 V. When the open-drain pin is active, it will drive low. When the pin is inactive, the trace will be pulled up to 5.0 V by the resistor. The open-drain pin will only drive low or tri-state; it will never drive high. The rise time is dependent on the value of the pull-up resistor and load impedance. The I_{OL} current specification should be considered when selecting a pull-up resistor.

Output pins on 5.0-V FLEX 10K devices with V_{CCIO} = 3.3 V or 5.0 V (with a pull-up resistor to the 5.0-V supply) can also drive 5.0-V CMOS input pins. In this case, the pull-up transistor will turn off when the pin voltage exceeds 3.3 V. Therefore, the pin does not have to be open-drain.

MultiVolt I/O Interface

The FLEX 10K device architecture supports the MultiVolt I/O interface feature, which allows FLEX 10K devices to interface with systems of differing supply voltages. These devices have one set of V_{CC} pins for internal operation and input buffers (VCCINT) and another set for I/O output drivers (VCCIO).

Table 13. FLEX 10K JTAG Instructions

JTAG Instruction	Description
SAMPLE/PRELOAD	Allows a snapshot of signals at the device pins to be captured and examined during normal device operation, and permits an initial data pattern output at the device pins.
EXTEST	Allows the external circuitry and board-level interconnections to be tested by forcing a test pattern at the output pins and capturing test results at the input pins.
BYPASS	Places the 1-bit bypass register between the `TDI` and `TDO` pins, which allows the BST data to pass synchronously through a selected device to adjacent devices during normal device operation.
USERCODE	Selects the user electronic signature (USERCODE) register and places it between the `TDI` and `TDO` pins, allowing the USERCODE to be serially shifted out of `TDO`.
IDCODE	Selects the IDCODE register and places it between `TDI` and `TDO`, allowing the IDCODE to be serially shifted out of `TDO`.
ICR Instructions	These instructions are used when configuring a FLEX 10K device via JTAG ports with a BitBlaster, or ByteBlasterMV or MasterBlaster download cable, or using a Jam File (**.jam**) or Jam Byte-Code File (**.jbc**) via an embedded processor.

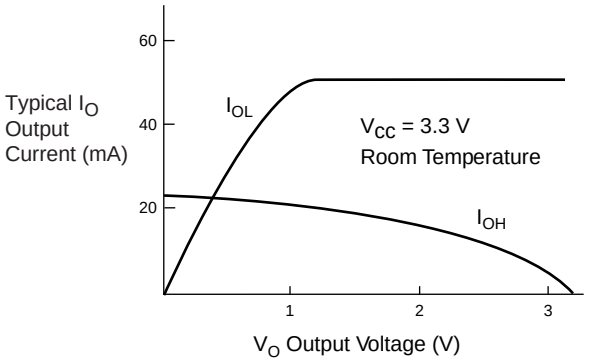
The instruction register length of FLEX 10K devices is 10 bits. The USERCODE register length in FLEX 10K devices is 32 bits; 7 bits are determined by the user, and 25 bits are predetermined. Tables 14 and 15 show the boundary-scan register length and device IDCODE information for FLEX 10K devices.

Table 14. FLEX 10K Boundary-Scan Register Length

Device	Boundary-Scan Register Length
EPF10K10, EPF10K10A	480
EPF10K20	624
EPF10K30, EPF10K30A	768
EPF10K40	864
EPF10K50, EPF10K50V	960
EPF10K70	1,104
EPF10K100, EPF10K100A	1,248
EPF10K130V	1,440
EPF10K250A	1,440

Figure 21 shows the typical output drive characteristics of EPF10K50V and EPF10K130V devices.

Figure 21. Output Drive Characteristics of EPF10K50V & EPF10K130V Devices



Tables 26 through 31 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 3.3-V FLEX 10K devices.

Table 26. FLEX 10KA 3.3-V Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	Supply voltage	With respect to ground *(2)*	–0.5	4.6	V
V_I	DC input voltage		–2.0	5.75	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	Ceramic packages, under bias		150	° C
		PQFP, TQFP, RQFP, and BGA packages, under bias		135	° C

Table 34. EAB Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
$t_{EABDATA1}$	Data or address delay to EAB for combinatorial input	
$t_{EABDATA2}$	Data or address delay to EAB for registered input	
t_{EABWE1}	Write enable delay to EAB for combinatorial input	
t_{EABWE2}	Write enable delay to EAB for registered input	
t_{EABCLK}	EAB register clock delay	
t_{EABCO}	EAB register clock-to-output delay	
$t_{EABBYPASS}$	Bypass register delay	
t_{EABSU}	EAB register setup time before clock	
t_{EABH}	EAB register hold time after clock	
t_{AA}	Address access delay	
t_{WP}	Write pulse width	
t_{WDSU}	Data setup time before falling edge of write pulse	*(5)*
t_{WDH}	Data hold time after falling edge of write pulse	*(5)*
t_{WASU}	Address setup time before rising edge of write pulse	*(5)*
t_{WAH}	Address hold time after falling edge of write pulse	*(5)*
t_{WO}	Write enable to data output valid delay	
t_{DD}	Data-in to data-out valid delay	
t_{EABOUT}	Data-out delay	
t_{EABCH}	Clock high time	
t_{EABCL}	Clock low time	

Notes to tables:

(1) Microparameters are timing delays contributed by individual architectural elements. These parameters cannot be measured explicitly.

(2) Operating conditions: V_{CCIO} = 5.0 V ± 5% for commercial use in FLEX 10K devices.
V_{CCIO} = 5.0 V ± 10% for industrial use in FLEX 10K devices.
V_{CCIO} = 3.3 V ± 10% for commercial or industrial use in FLEX 10KA devices.

(3) Operating conditions: V_{CCIO} = 3.3 V ± 10% for commercial or industrial use in FLEX 10K devices.
V_{CCIO} = 2.5 V ± 0.2 V for commercial or industrial use in FLEX 10KA devices.

(4) Operating conditions: V_{CCIO} = 2.5 V, 3.3 V, or 5.0 V.

(5) Because the RAM in the EAB is self-timed, this parameter can be ignored when the WE signal is registered.

(6) EAB macroparameters are internal parameters that can simplify predicting the behavior of an EAB at its boundary; these parameters are calculated by summing selected microparameters.

(7) These parameters are worst-case values for typical applications. Post-compilation timing simulation and timing analysis are required to determine actual worst-case performance.

(8) External reference timing parameters are factory-tested, worst-case values specified by Altera. A representative subset of signal paths is tested to approximate typical device applications.

(9) Contact Altera Applications for test circuit specifications and test conditions.

(10) These timing parameters are sample-tested only.

Figures 29 and 30 show the asynchronous and synchronous timing waveforms, respectively, for the EAB macroparameters in Table 34.

Figure 29. EAB Asynchronous Timing Waveforms

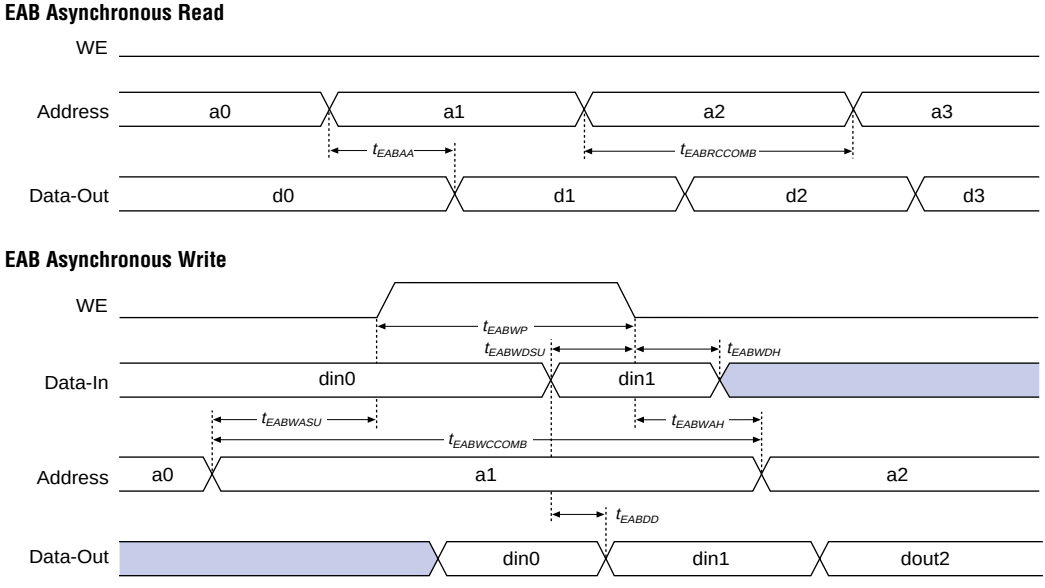


Table 42. EPF10K10 & EPF10K20 Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{EABAA}		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		17.0		ns
$t_{EABRCREG}$	9.7		11.9		ns
t_{EABWP}	5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		9.0		ns
$t_{EABWCREG}$	13.0		16.0		ns
t_{EABDD}		10.0		12.5	ns
$t_{EABDATACO}$		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		ns
$t_{EABWESU}$	5.5		5.8		ns
t_{EABWEH}	0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.8		ns
t_{EABWDH}	0.0		0.0		ns
$t_{EABWASU}$	2.1		2.7		ns
t_{EABWAH}	0.0		0.0		ns
t_{EABWO}		9.5		11.8	ns

Table 59. EPF10K70 Device EAB Internal Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.3		1.5		1.9	ns
$t_{EABDATA2}$		4.3		4.8		6.0	ns
t_{EABWE1}		0.9		1.0		1.2	ns
t_{EABWE2}		4.5		5.0		6.2	ns
t_{EABCLK}		0.9		1.0		2.2	ns
t_{EABCO}		0.4		0.5		0.6	ns
$t_{EABBYPASS}$		1.3		1.5		1.9	ns
t_{EABSU}	1.3		1.5		1.8		ns
t_{EABH}	1.8		2.0		2.5		ns
t_{AA}		7.8		8.7		10.7	ns
t_{WP}	5.2		5.8		7.2		ns
t_{WDSU}	1.4		1.6		2.0		ns
t_{WDH}	0.3		0.3		0.4		ns
t_{WASU}	0.4		0.5		0.6		ns
t_{WAH}	0.9		1.0		1.2		ns
t_{WO}		4.5		5.0		6.2	ns
t_{DD}		4.5		5.0		6.2	ns
t_{EABOUT}		0.4		0.5		0.6	ns
t_{EABCH}	4.0		4.0		4.0		ns
t_{EABCL}	5.2		5.8		7.2		ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 64 through 70 show EPF10K100 device internal and external timing parameters.

Table 64. EPF10K100 Device LE Timing Microparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.5		1.5		2.0	ns
t_{CLUT}		0.4		0.4		0.5	ns
t_{RLUT}		1.6		1.6		2.0	ns
t_{PACKED}		0.9		0.9		1.3	ns
t_{EN}		0.9		0.9		1.2	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		1.1		1.1		1.4	ns
t_{CGENR}		1.2		1.2		1.5	ns
t_{CASC}		1.1		1.1		1.3	ns
t_{C}		0.8		0.8		1.0	ns
t_{CO}		1.0		1.0		1.4	ns
t_{COMB}		0.5		0.5		0.7	ns
t_{SU}	2.1		2.1		2.6		ns
t_{H}	2.3		2.3		3.1		ns
t_{PRE}		1.0		1.0		1.4	ns
t_{CLR}		1.0		1.0		1.4	ns
t_{CH}	4.0		4.0		4.0		ns
t_{CL}	4.0		4.0		4.0		ns

Table 66. EPF10K100 Device EAB Internal Microparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.5		1.5		1.9	ns
$t_{EABDATA2}$		4.8		4.8		6.0	ns
t_{EABWE1}		1.0		1.0		1.2	ns
t_{EABWE2}		5.0		5.0		6.2	ns
t_{EABCLK}		1.0		1.0		2.2	ns
t_{EABCO}		0.5		0.5		0.6	ns
$t_{EABBYPASS}$		1.5		1.5		1.9	ns
t_{EABSU}	1.5		1.5		1.8		ns
t_{EABH}	2.0		2.0		2.5		ns
t_{AA}		8.7		8.7		10.7	ns
t_{WP}	5.8		5.8		7.2		ns
t_{WDSU}	1.6		1.6		2.0		ns
t_{WDH}	0.3		0.3		0.4		ns
t_{WASU}	0.5		0.5		0.6		ns
t_{WAH}	1.0		1.0		1.2		ns
t_{WO}		5.0		5.0		6.2	ns
t_{DD}		5.0		5.0		6.2	ns
t_{EABOUT}		0.5		0.5		0.6	ns
t_{EABCH}	4.0		4.0		4.0		ns
t_{EABCL}	5.8		5.8		7.2		ns

Table 69. EPF10K100 Device External Timing Parameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		19.1		19.1		24.2	ns
t_{INSU} *(2)*, *(3)*, *(4)*	7.8		7.8		8.5		ns
t_{OUTCO} *(3)*, *(4)*	2.0	11.1	2.0	11.1	2.0	14.3	ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{INSU} *(2)*, *(3)*, *(5)*	6.2		–		–		ns
t_{OUTCO} *(3)*, *(5)*	2.0	6.7		–		–	ns

Table 70. EPF10K100 Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ *(4)*	8.1		8.1		10.4		ns
$t_{INHBIDIR}$ *(4)*	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$ *(4)*	2.0	11.1	2.0	11.1	2.0	14.3	ns
$t_{XZBIDIR}$ *(4)*		15.3		15.3		18.4	ns
$t_{ZXBIDIR}$ *(4)*		15.3		15.3		18.4	ns
$t_{INSUBIDIR}$ *(5)*	9.1		–		–		ns
$t_{INHBIDIR}$ *(5)*	0.0		–		–		ns
$t_{OUTCOBIDIR}$ *(5)*	2.0	7.2	–	–	–	–	ns
$t_{XZBIDIR}$ *(5)*		14.3		–		–	ns
$t_{ZXBIDIR}$ *(5)*		14.3		–		–	ns

Notes to tables:

(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.
(4) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
(5) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 78 through 84 show EPF10K130V device internal and external timing parameters.

Table 78. EPF10K130V Device LE Timing Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.3		1.8		2.3	ns
t_{CLUT}		0.5		0.7		0.9	ns
t_{RLUT}		1.2		1.7		2.2	ns
t_{PACKED}		0.5		0.6		0.7	ns
t_{EN}		0.6		0.8		1.0	ns
t_{CICO}		0.2		0.3		0.4	ns
t_{CGEN}		0.3		0.4		0.5	ns
t_{CGENR}		0.7		1.0		1.3	ns
t_{CASC}		0.9		1.2		1.5	ns
t_{C}		1.9		2.4		3.0	ns
t_{CO}		0.6		0.9		1.1	ns
t_{COMB}		0.5		0.7		0.9	ns
t_{SU}	0.2		0.2		0.3		ns
t_{H}	0.0		0.0		0.0		ns
t_{PRE}		2.4		3.1		3.9	ns
t_{CLR}		2.4		3.1		3.9	ns
t_{CH}	4.0		4.0		4.0		ns
t_{CL}	4.0		4.0		4.0		ns

Table 88. EPF10K10A Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		8.1		9.8		13.1	ns
$t_{EABRCCOMB}$	8.1		9.8		13.1		ns
$t_{EABRCREG}$	5.8		6.9		9.3		ns
t_{EABWP}	2.0		2.4		3.2		ns
$t_{EABWCCOMB}$	3.5		4.2		5.6		ns
$t_{EABWCREG}$	9.4		11.2		14.8		ns
t_{EABDD}		6.9		8.3		11.0	ns
$t_{EABDATACO}$		1.3		1.5		2.0	ns
$t_{EABDATASU}$	2.4		3.0		3.9		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	4.1		4.9		6.5		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.4		1.6		2.2		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	2.5		3.0		4.1		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		6.2		7.5		9.9	ns

Table 89. EPF10K10A Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		4.2		5.0		6.5	ns
t_{DIN2LE}		2.2		2.6		3.4	ns
$t_{DIN2DATA}$		4.3		5.2		7.1	ns
$t_{DCLK2IOE}$		4.2		4.9		6.6	ns
$t_{DCLK2LE}$		2.2		2.6		3.4	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		2.2		2.4		2.9	ns
$t_{SAMECOLUMN}$		0.8		1.0		1.4	ns
$t_{DIFFROW}$		3.0		3.4		4.3	ns
$t_{TWOROWS}$		5.2		5.8		7.2	ns
$t_{LEPERIPH}$		1.8		2.2		2.8	ns
$t_{LABCARRY}$		0.5		0.5		0.7	ns
$t_{LABCASC}$		0.9		1.0		1.5	ns

Table 90. EPF10K10A External Reference Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		10.0		12.0		16.0	ns
t_{INSU} *(2)*, *(3)*	1.6		2.1		2.8		ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.8	2.0	6.9	2.0	9.2	ns

Table 91. EPF10K10A Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.4		3.3		4.5		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	5.8	2.0	6.9	2.0	9.2	ns
$t_{XZBIDIR}$		6.3		7.5		9.9	ns
$t_{ZXBIDIR}$		6.3		7.5		9.9	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 37 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

ClockLock & ClockBoost Timing Parameters

For the ClockLock and ClockBoost circuitry to function properly, the incoming clock must meet certain requirements. If these specifications are not met, the circuitry may not lock onto the incoming clock, which generates an erroneous clock within the device. The clock generated by the ClockLock and ClockBoost circuitry must also meet certain specifications. If the incoming clock meets these requirements during configuration, the ClockLock and ClockBoost circuitry will lock onto the clock during configuration. The circuit will be ready for use immediately after configuration. Figure 31 illustrates the incoming and generated clock specifications.

Figure 31. Specifications for the Incoming & Generated Clocks

The t_I parameter refers to the nominal input clock period; the t_O parameter refers to the nominal output clock period.

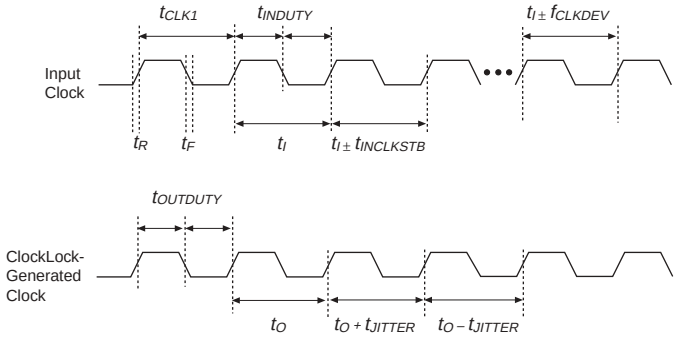


Table 113 summarizes the ClockLock and ClockBoost parameters.

Table 113. ClockLock & ClockBoost Parameters (Part 1 of 2)

Symbol	Parameter	Min	Typ	Max	Unit
t_R	Input rise time			2	ns
t_F	Input fall time			2	ns
t_{INDUTY}	Input duty cycle	45		55	%
f_{CLK1}	Input clock frequency (ClockBoost clock multiplication factor equals 1)	30		80	MHz
t_{CLK1}	Input clock period (ClockBoost clock multiplication factor equals 1)	12.5		33.3	ns
f_{CLK2}	Input clock frequency (ClockBoost clock multiplication factor equals 2)	16		50	MHz
t_{CLK2}	Input clock period (ClockBoost clock multiplication factor equals 2)	20		62.5	ns

101 Innovation Drive
San Jose, CA 95134
(408) 544-7000
http://www.altera.com
Applications Hotline:
(800) 800-EPLD
Customer Marketing:
(408) 544-7104
Literature Services:
lit_req@altera.com